

Enxiu Wu

List of Publications by Year in descending order

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Version: 2024-02-01

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papers

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citations

687363

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all docs

24
docs citations

24
times ranked

1136
citing authors

#	ARTICLE	IF	CITATIONS
1	Dielectric engineering enable to lateral anti-ambipolar MoTe ₂ heterojunction. Nanotechnology, 2022, 33, 175704.	2.6	8
2	Flash memory based on MoTe ₂ /boron nitride/graphene semi-floating gate heterostructure with non-volatile and dynamically tunable polarity. Nano Research, 2022, 15, 6507-6514.	10.4	6
3	Modulation of MoTe ₂ /MoS ₂ van der Waals heterojunctions for multifunctional devices using N ₂ O plasma with an opposite doping effect. Nanoscale, 2021, 13, 7851-7860.	5.6	5
4	Gate-tunable van der Waals heterostructure based on semimetallic WTe ₂ and semiconducting MoTe ₂ . Applied Physics Letters, 2021, 118, .	3.3	10
5	UV light modulated synaptic behavior of MoTe ₂ /BN heterostructure. Nanotechnology, 2021, 32, 475207.	2.6	3
6	Side-liquid-gated electrochemical transistors and their neuromorphic applications. Journal of Materials Chemistry C, 2021, 9, 16655-16663.	5.5	11
7	Multi-level flash memory device based on stacked anisotropic ReS ₂ boron nitride-graphene heterostructures. Nanoscale, 2020, 12, 18800-18806.	5.6	27
8	Frequency doubler based on a single MoTe ₂ /MoS ₂ anti-ambipolar heterostructure. Applied Physics Letters, 2020, 117, .	3.3	20
9	Non-volatile programmable homogeneous lateral MoTe ₂ junction for multi-bit flash memory and high-performance optoelectronics. Nano Research, 2020, 13, 3445-3451.	10.4	11
10	Tunable and nonvolatile multibit data storage memory based on MoTe ₂ /boron nitride/graphene heterostructures through contact engineering. Nanotechnology, 2020, 31, 485205.	2.6	11
11	Multifunctional anti-ambipolar p-n junction based on MoTe ₂ /MoS ₂ heterostructure. Applied Physics Letters, 2019, 115, .	3.3	35
12	Dynamically controllable polarity modulation of MoTe ₂ field-effect transistors through ultraviolet light and electrostatic activation. Science Advances, 2019, 5, eaav3430.	10.3	96
13	Gate-Tunable Photodetection/Voltaic Device Based on BP/MoTe ₂ Heterostructure. ACS Applied Materials & Interfaces, 2019, 11, 14215-14221.	8.0	34
14	Photoinduced Doping To Enable Tunable and High-Performance Anti-Ambipolar MoTe ₂ /MoS ₂ Heterotransistors. ACS Nano, 2019, 13, 5430-5438.	14.6	73
15	The effect of air stable n-doping through mild plasma on the mechanical property of WSe ₂ layers. Nanotechnology, 2018, 29, 175703.	2.6	5
16	Volatile organic compounds discrimination based on dual mode detection. Nanotechnology, 2018, 29, 245502.	2.6	5
17	Specific and Highly Sensitive Detection of Ketone Compounds Based on p-Type MoTe ₂ under Ultraviolet Illumination. ACS Applied Materials & Interfaces, 2018, 10, 35664-35669.	8.0	34
18	Anomalous Acoustoelectric Currents in Few-Layer Black Phosphorus Nanocrystals. IEEE Nanotechnology Magazine, 2018, 17, 590-595.	2.0	8

#	ARTICLE	IF	CITATIONS
19	Acoustically enhanced photodetection by a black phosphorus MoS_2 van der Waals heterojunction p -n diode. <i>Nanoscale</i> , 2018, 10, 10148-10153.	5.6	31
20	Ultrasensitive and Fully Reversible NO_2 Gas Sensing Based on p-Type MoTe_2 under Ultraviolet Illumination. <i>ACS Sensors</i> , 2018, 3, 1719-1726.	7.8	135
21	Highly-sensitive gas sensor based on two-dimensional material field effect transistor. <i>Nanotechnology</i> , 2018, 29, 435502.	2.6	32
22	Enhancing electronic and optoelectronic performances of tungsten diselenide by plasma treatment. <i>Nanoscale</i> , 2018, 10, 12436-12444.	5.6	30
23	Contact Engineering of Molybdenum Ditelluride Field Effect Transistors through Rapid Thermal Annealing. <i>ACS Applied Materials & Interfaces</i> , 2017, 9, 30107-30114.	8.0	37
24	Enhanced Sensitivity of MoTe_2 Chemical Sensor through Light Illumination. <i>Micromachines</i> , 2017, 8, 155.	2.9	30